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U.S. UTILITY Patent Application

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APPLICATION NO.	CONT/PRIOR	CLASS	SUBCLASS	ART UNIT	EXAMINER
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03/3044/2		438	1799	2812	
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Stephane Martel Yan Riopel Sebastien Michel Luc Ouellet

Method of making high-voltage bipolar/CMOS/DMOS (BCD) devices

ISSUING CLASSIFICATION ORIGINAL CROSS REFERENCE(S) CLASS SUBCLASS CLASS SUBCLASS (ONE SUBCLASS PER BLOCK) INTERNATIONAL CLASSIFICATION Continued on Issue Slip Inside File Jacket

TERMINAL		DRAWINGS			CLAIMS ALLOWED		
DISCLAIMER	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.		
The term of this patent subsequent to(date)			-	NOTICE OF ALI	LOWANCE MAILED		
has been disclaimed.	(Assistant E	Examiner)	(Date)				
The term of this patent shall not extend beyond the expiration date							
of U.S Patent. No.	•			ISSUE FEE			
				Amount Due	Date Paid		
	(Primary Examiner)		(Date)	i			
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